

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the specification:

On page 3, paragraph 7 has been amended as follows:

The ideal etching structure is a pure tunnel-like etch with defined and uniform tunnel diameters and without any undesirable pitting of the foil. As tunnel density (*i.e.*, the number of tunnels per square centimeter) is increased, a corresponding enlargement of the overall surface area will occur. Larger surface area results in higher overall capacitance. However, as tunnel density increases, more of the aluminum foil is removed, reducing the strength of the remaining foil. Therefore a [comprise] compromise must be made between foil strength and capacitance gain.